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UTILITY APPLICATION FOR UNITED STATES PATENT
FOR
METHOD FOR RELEASING STRESS DURING SEMICONDUCTOR
DEVICE FABRICATION

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METHOD FOR RELEASING STRESS DURING SEMICONDUCTOR DEVICE FABRICATION

Field of the Invention

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The present invention relates to semiconductor device fabrication; and, more particularly, to a method for fabricating a semiconductor device having a gate electrode with a tungsten layer.

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Description of related Arts

Stacked gate structures with a poly-silicon layer, a tungsten (W) layer and a tungsten nitride (WN) layer are used to reduce resistance of gate electrodes.

However, the stacked gate structure mentioned above has some drawbacks such as an interfacial reaction of the poly-silicon layer, the tungsten layer and the tungsten nitride layer during a re-oxidization process using H₂O or O₂, an abrupt volume expansion by an oxidation of the tungsten layer, and particle generation. Herein, the re-oxidization process of the tungsten nitride layer is carried out to recover a micro-trench created on a gate oxide layer during an etching process and a loss generated thereby, oxidize the remnant poly-silicon layer remaining on a silicon substrate, and improve reliability of the semiconductor device by increasing thickness of the gate oxide layer formed on an edge area of the gate electrode.

The thickness and quality of the gate oxide layer are factors affecting a hot carrier property, a sub-threshold voltage property such as a leakage current property and a gate induced drain leakage (GIDL) property, a punch-through property and device operating speed.

Therefore, the re-oxidization process is an essential requisite of semiconductor device fabrication.

To overcome the aforementioned drawbacks, a selective oxidation process is suggested. The selective oxidation
5 process oxidizes only the poly-silicon layer and the silicon substrate without oxidizing the tungsten layer and the tungsten nitride layer in a H₂ rich ambient including H₂O.

In short, the selective oxidation process is used for
10 forming a gate bird's beak required for obtaining superior GILD property.

Fig. 1A is a flowchart showing a method for fabricating a semiconductor device including the gate electrode having a tungsten layer in accordance with the
15 prior art. Fig. 1B is a cross-sectional diagram showing the semiconductor device according to a series of the processes shown in Fig. 1A.

As shown in Fig. 1A, the prior art related to semiconductor device fabrication comprises the following
20 processes: a gate electrode patterning process S1 for forming a stacked gate electrode deposited sequentially with the poly-silicon layer, the tungsten nitride layer and the tungsten layer; the selective oxidation process S2 adopting a rapid thermal process (RTP); a gate sealing
25 nitride layer deposition process S3; a gate spacer oxide layer deposition process S4; an inter layer dielectric layer deposition process S5 using boro-phosphor-silicate-glass (BPSG); a RTP for activating source/drain regions S6; and a heat treatment process S7 for performing the
30 inter layer dielectric layer flow process.

Referring to Fig. 1B, a gate oxide layer 12 is grown on a semiconductor substrate 11 on which a field oxide layer (FOX) is formed. Next, the poly-silicon layer 13,

the tungsten nitride layer 14, the tungsten layer 15, and a hard mask 16 are sequentially deposited on the gate oxide layer 12. Next, the hard mask 16, the tungsten layer 15, the tungsten nitride layer 14 and the poly-silicon layer 13 are etched sequentially in order to predetermine the gate electrode.

As a next step, the selective oxidation process is carried out in a H_2O ambient for the purpose of forming the gate bird's beak. At this time, a silicon oxide layer 18A is formed on both lateral sides of the poly-silicon layer 13 by carrying out the selective oxidation process, and a silicon oxide layer 18B is also formed on the semiconductor substrate 11.

Next, the above structure including the gate electrode is covered with the gate sealing nitride layer 19 to prevent an oxidation of the tungsten layer 15 while proceeding a heat treatment process.

However, the semiconductor device fabricated in accordance with the prior art has a drawback such as a deterioration of a data retention time property. In short, a trap or a defect is generated at a cell conjunction due to a thermal stress developed by an abrupt change in thermal history created on a wafer especially during the RTP process, and the trap or defect acts as a path for a leakage current. Accordingly, the data retention time property is deteriorated, and consequently, a refresh time fail is induced.

As shown in Fig. 1B, for a DRAM semiconductor device having a triple stack layer constituted with the poly-silicon layer, the tungsten nitride layer, and tungsten layer, the selective oxidation process should be carried out to obtain the GILD property. At this time, the selective oxidation process uses a method that adopts the

RTP process having a rising and falling thermal history. Accordingly, the semiconductor substrate is affected by a stress exerted by the RTP process. For instance, a trap site or a defect is created at a gate channel or a cell
5 conjunction, and eventually, increasing a conjunction leakage.

Now, in a 0.13 μm and less than 0.13 μm semiconductor technology, the gate sealing nitride deposition process for protecting the tungsten layer and
10 follow-up processes are carried out without releasing the stress occurring after the selective oxidation process is performed. Therefore, the stress becomes more serious and accordingly, a deterioration of a refresh time is manifested more frequently.

15 Fig 2 is a graph showing a stress history measured while a series of processes in accordance with the prior art are performed. Herein, an abscissa shows each name of the processes and an ordinate shows a stress level measured during each of the processes. In addition, the
20 graph shows thermal stress values measured at a gate edge, a spacer edge, a top corner of a shallow trench isolation STI or FOX top corner, and a shallow trench isolation STI or FOX, and a bottom corner of the STI or FOX.

As shown in Fig 2, it is evident that the stress
25 becomes more serious during a gate oxide layer formation process, a gate electrode patterning process and the selective oxidation process than the stress exerted during a trench formation process for forming the STI and a well annealing process. However, the stress starts being
30 released during an inter layer dielectric layer (ILD1) flow process. Especially, it is observed that a strong stress is exerted during the selective oxidation process (X).

Accordingly, a special method for technically releasing the stress exerted during the selective oxidation process is required.

Summary of the Invention

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It is, therefore, an object of the present invention to provide a method for releasing stress exerted during a semiconductor device fabricating process.

In accordance with an aspect of the present
10 invention, there is provided the method for releasing the stress, including: forming a stack layer deposited on a semiconductor sequentially with a gate oxide layer, a poly-silicon layer, a tungsten layer, and a hard mask; carrying out a selective oxidation process, wherein the
15 poly-silicon layer of the stack layer is only oxidized; performing a heat treatment process for releasing a stress exerted during the selective oxidation process; and carrying out a process for forming a gate sealing nitride layer on the stack layer heat-treated.

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Brief Description of the Drawings

Other objects and aspects of the invention will become apparent from the following description of the
25 embodiments with reference to the accompanying drawings, in which:

Fig. 1A is a flowchart illustrating a method for fabricating a semiconductor device including a gate electrode with a tungsten layer in accordance with the
30 prior art;

Fig. 1B is a cross-sectional view of the semiconductor device fabricated in accordance with the method illustrated in Fig. 1A;

Fig. 2 is a diagram showing a history of the stress exerted as a series of processes are carried out in accordance with a prior art;

Fig. 3 is a flowchart showing a method for
5 fabricating a semiconductor device in accordance with a first preferred embodiment of the present invention;

Fig. 4 is a flowchart showing a method for fabricating a semiconductor device in accordance with a second preferred embodiment of the present invention;

10 Fig. 5 is a diagram showing a thermal history tendency of a series of deposition processes for a gate sealing nitride layer shown in Fig. 3 and Fig. 4;

Fig. 6 is a diagram showing a flowchart of a method for fabricating a semiconductor device in accordance with
15 a third preferred embodiment of the present invention; and

Fig. 7 is a graph showing a stress change before and after a heat treatment process.

Detailed Description of the Preferred Embodiments

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Hereinafter, a method is disclosed for releasing stress exerted during fabrication of a semiconductor device including a gate electrode with a tungsten layer.

Fig. 3 is a flowchart showing a method for
25 fabricating a semiconductor device in accordance with a first preferred embodiment of the present invention.

Referring to Fig. 3, the semiconductor device in accordance with the first preferred embodiment of the present invention is fabricated through the following
30 sequential process steps: a gate electrode patterning process S11 forming a gate electrode stacked sequentially with a poly-silicon layer, a tungsten nitride layer and a tungsten layer; a selective oxidation process S12 adopting

a rapid thermal process (RTP); a vacuum heat treatment process S13 using a low pressure chemical vapor deposition (LPCVD) furnace; a gate sealing nitride layer deposition process S14; a gate spacer oxide layer deposition process S15; an inter layer dielectric layer (ILD1) deposition process S16 using a boro-phospho-silicate-glass (BPSG); another RTP for activating source/drain regions S17; and a heat treatment process S18 for the inter layer dielectric layer (ILD1) flow. Herein, both the vacuum heat treatment process S13 and the gate sealing nitride layer deposition process S14 using the LPCVD furnace are carried out under an in-situ method.

As shown in Fig. 3, the vacuum heat treatment process S13 using the LPCVD furnace is carried out right after the selective oxidation process S12 adopting the rapid thermal process. Herein, the vacuum heat treatment is used for not only removing a trap or defect generated at a cell conjunction of a semiconductor substrate but also releasing stress caused by the RTP process used during selective oxidation process S12, wherein the cell conjunction is formed at a bottom of the gate oxide layer.

As a next step, the gate sealing nitride layer deposition process S14 is performed to prevent the tungsten layer from being oxidized abnormally during succeeding processes. At this time, the gate sealing nitride layer is deposited under the in-situ method by using the LPCVD furnace. More specifically, the gate sealing nitride layer is deposited under the in-situ method after gradually decreasing a heat treatment temperature to a target temperature during the vacuum heat treatment process S13 using the LPCVD furnace. Eventually, since both of the vacuum heat treatment process S13 and the gate sealing nitride layer deposition

process S14 using the LPCVD furnace are carried out under the in-situ method, the trap or defect generated by the stress induced during the selective oxidation process S12 can be cured and thereby, the leakage path of the cell conjunction is removed by recovering a distorted semiconductor substrate. Herein a temperature of the LPCVD furnace is increased above about 750° C at a slowly rising rate and decreased thereafter in order to recover the distorted semiconductor substrate.

In addition, the vacuum heat treatment process S13 using the LPCVD furnace is performed at a high temperature and at a normal pressure in a nitrogen gas ambient for a predetermined time. Accordingly, a series of the processes mentioned above impedes impurities from existing in the nitrogen gas and the tungsten layer from abnormally being oxidized at a normal pressure. Furthermore, it is possible to obtain a simplified process for fabricating the semiconductor device by using the in-situ vacuum heat treatment method during the gate sealing nitride layer deposition.

The in-situ method of the heat treatment process and the gate sealing nitride layer deposition process will now be described more specifically. First of all, the semiconductor substrate to which the selective oxidation process is implemented is loaded into the LPCVD furnace and heat-treated by increasing the temperature of the LPCVD furnace from normal room temperature to a target temperature in vacuum ambient. Next, the gate sealing nitride layer is deposited while the temperature of the LPCVD furnace is decreased from the heat treatment temperature to a deposition temperature for depositing the gate sealing nitride layer. As a last step, the temperature of the LPCVD furnace is decreased to the

normal temperature and the semiconductor device is unloaded from the LPCVD furnace. Herein, the heat treatment temperature ranges from about 750° C to about 1000° C and the vacuum ambient has a pressure of about 10^{-3} torr to about 10^{-2} torr. Preferably, the rising rate of the temperature for the heat treatment process ranges from about 3° C/min to about 25° C/min and a falling rate of the temperature during the gate sealing nitride layer deposition ranges from 3° C/min to about 25° C/min. Also, the total heat treatment time is within a range of about 10 minutes to about 240 minutes.

Fig. 4 is a flow chart showing a method for fabricating a semiconductor device in accordance with a second preferred embodiment of the present invention.

Referring to Fig. 4, the semiconductor device in accordance with the second preferred embodiment of the present invention is fabricated through the following sequential processes: a gate electrode patterning process S21 forming a stacked gate electrode stacked sequentially with a poly-silicon layer, a tungsten nitride layer, and a tungsten layer; a selective oxidation process S22 adopting a RTP; a vacuum heat treatment process S23 using a low pressure chemical vapor deposition (LPCVD) furnace; a gate sealing nitride layer deposition process S24 using the LPCVD furnace; a gate spacer oxide layer deposition process S25; an ILD1 deposition process using BPSG S26; a RTP for activating source/drain regions S27; and a heat treatment process for the ILD1 flow S28. Herein, the vacuum heat treatment process S23 and the gate sealing nitride layer deposition process S22 both using the LPCVD furnace are carried out under an ex-situ method.

As shown in Fig. 4, the vacuum heat treatment process S23 using the LPCVD furnace is carried out right after the

selective oxidation process S22 adopting the RTP. Herein, the vacuum heat treatment process S23 is for not only curing a trap or defect generated at a cell conjunction of a semiconductor substrate formed at a bottom of the gate oxide layer but also releasing a stress caused by the RTP used during the selective oxidation process S22.

As a next step, the gate sealing nitride layer deposition process S24 is performed in the same LPCVD furnace or two different LPCVD furnaces under the ex-situ method so as to prevent the tungsten layer from being oxidized abnormally during succeeding processes.

More specifically, the semiconductor substrate at which the selective oxidation process has been performed is loaded in a first LPCVD furnace. Herein, a temperature of the first LPCVD furnace is slowly increased and the semiconductor substrate is heat-treated in a vacuum ambient. Next, the temperature of the first LPCVD furnace is decreased to a room temperature and the semiconductor substrate is unloaded from the first LPCVD furnace. As a next step, the unloaded semiconductor substrate is loaded again into the first LPCVD furnace or a second LPCVD furnace, wherein a gate sealing nitride layer is deposited on the semiconductor substrate. At this time, the heat treatment temperature ranges from about 750° C to about 1000° C, and the vacuum ambient has a pressure of about 10^{-3} torr to about 10^{-2} torr. Preferably, the rising rate of the heat treatment temperature is from about 3° C/min to about 25° C/min, the falling rate of the deposition temperature ranges from about 1° C/min to about 20° C/min. Also, the total heat treatment time is from about 10 mins to about 240 mins.

Fig. 5 is a diagram showing a thermal history tendency of the deposition processes for the gate sealing

nitride layer shown in Fig. 3 and Fig. 4.

Referring to Fig. 5, the semiconductor substrate is loaded into the LPCVD furnace and then is heat-treated through gradually increasing a temperature of the LPCVD furnace. The temperature of the LPCVD is decreased after finishing the heat treatment and the gate sealing nitride layer is deposited thereafter. As a last step, the temperature of the LPCVD furnace is decreased to room temperature at which the semiconductor substrate was loaded and the semiconductor substrate is unloaded from the LPCVD furnace. At this time, an ambient in the LPCVD furnace is kept in a vacuum condition until depositing the gate sealing nitride layer.

Fig. 6 is a flow chart showing a method for fabricating a semiconductor device in accordance with a third preferred embodiment of the present invention.

Referring to Fig. 6, the semiconductor device in accordance with the third preferred embodiment of the present invention is fabricated through the following sequential processes: a gate electrode patterning process S31 forming a stacked gate electrode stacked sequentially with a poly-silicon layer, a tungsten nitride layer, and a tungsten layer; a selective oxidation process adopting a RTP S32; a gate sealing nitride layer deposition process S33; a heat treatment process S34 using a low pressure chemical vapor deposition (LPCVD) furnace or an annealing furnace; a gate spacer oxide layer deposition process S35; an inter layer dielectric layer(ILD1) deposition process S36 using the BPSG material; a RTP for activating source/drain regions S37; and a heat treatment process for the ILD1 flow.

As shown in Fig. 6, compared with the first and second preferred embodiments, the heat treatment process

S34 according to the third preferred embodiment is carried out in the LPCVD furnace or the annealing furnace in order to release a stress exerted after finishing the gate sealing nitride layer deposition process. Furthermore,
5 the heat treatment process mentioned above releases not only the stress exerted during the selective oxidation process S32 but also the stress exerted during the gate sealing nitride layer deposition process S33.

More specifically, the heat treatment process is
10 carried out in the LPCVD furnace or the annealing furnace in a vacuum ambient or in a nitrogen or inert gas ambient. At this time, a temperature for the heat treatment is gradually increased over about 750° C and is slowly decreased to room temperature after finishing the heat
15 treatment. In addition, the gate sealing nitride deposition process (S33) and the heat treatment process S34 are carried out in two same types of furnaces or two different types of furnaces under an ex-situ method.

In particular, there are two ex-situ methods used for
20 the gate sealing nitride layer deposition process S33 and the heat treatment process S34. Explaining the first ex-situ method in detail, in a first LPCVD furnace, the gate sealing nitride layer is deposited and the semiconductor substrate deposited with the gate sealing nitride layer is
25 loaded in a second LPCVD furnace. Next, a temperature of the second LPCVD furnace is gradually increased from room temperature to a target heat treatment temperature and the semiconductor substrate is heat-treated in a vacuum ambient. After finishing the heat treatment process, the
30 temperature of the second LPCVD furnace is decreased from the target heat treatment temperature to room temperature and the semiconductor substrate is unloaded thereafter. Explaining the second ex-situ method, the gate sealing

nitride layer is deposited on the semiconductor substrate in the LPCVD furnace and then, the semiconductor substrate is loaded in the annealing furnace. Next, a temperature of the annealing furnace is slowly increased from room
5 temperature to a target heat treatment temperature, and the semiconductor substrate is heat-treated in a vacuum ambient. Continuously, the heat treatment temperature is decreased to room temperature and the semiconductor substrate is unloaded thereafter.

10 During the heat treatment processes in accordance with the first ex-situ method and the second ex-situ method, the heat treatment temperature for the heat treatment process ranges from about 750° C to about 1000° C and the vacuum ambient has a pressure of about 10^{-3} torr
15 to about 10^{-2} torr. Particularly, a rising rate of the heat treatment temperature ranges from about 3° C/min to about 25° C/min, and a falling rate of the temperature until the semiconductor substrate is unloaded ranges from about 1° C/min to about 20° C/min. Also, a total heat
20 treatment time ranges from about 10 minutes to about 240 minutes.

Fig. 7 is a graph showing changes in the stress before and after a heat treatment process. An ordinate expresses the stress in a numerical value and an abscissa
25 shows each area at which each numerical value of the stress is measured. Concretely, the stress is measured at a gate electrode edge, a spacer edge, a top corner of a shallow trench isolation (STI or FOX) and a bottom corner of the STI.

30 As shown in Fig. 7, compared with a base case in which there is no heat treatment process for releasing the stress exerted after the selective oxidation process, a case of the heat treatment performed before depositing the

gate sealing nitride layer, another case of the heat treatment performed after depositing the same, and another case of the heat treatment performed before and after depositing the same show that the stress values measured
5 at each area are generally decreased.

Table. 1 shows a comparison of a refresh time (t_{REF}) value of the semiconductor device fabricated in accordance with the prior art with the t_{REF} value of the semiconductor device fabricated in accordance with the
10 present invention

Applied art	Improved portion/250ms (t_{REF})
Prior art	89.2ms/250ms
Vacuum heat treatment-30 secs (Present Invention)	91.3ms/250ms
Vacuum heat treatment-60 secs (Present Invention)	92.1ms/250ms

TABLE. 1

According to Table. 1, it is confirmed that the
15 refresh time is improved when the vacuum heat treatment process is used. Furthermore, it is also shown that the refresh time is improved as the vacuum heat treatment process time is increased.

While the present invention has been shown and
20 described with respect to the particular embodiments, it will be apparent to those skilled in the art that many changes and modification may be made without departing from the spirit and scope of the invention as defined in the appended claims.